

2N6400 Series

Preferred Device

Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half-wave silicon gate-controlled, solid-state devices are needed.

Features

- Glass Passivated Junctions with Center Gate Geometry for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts
- Pb-Free Packages are Available*



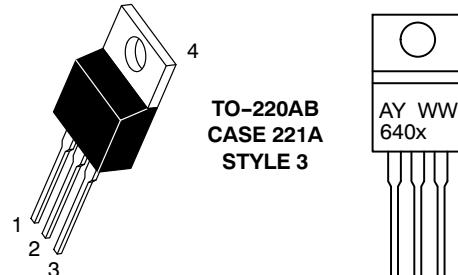
ON Semiconductor®

SCRs

**16 AMPERES RMS
50 thru 800 VOLTS**



MARKING DIAGRAM



x = 0, 1, 2, 3, 4 or 5
A = Assembly Location
Y = Year
WW = Work Week

PIN ASSIGNMENT	
1	Cathode
2	Anode
3	Gate
4	Anode

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

2N6400 Series

MAXIMUM RATINGS* (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave 50 to 60 Hz; Gate Open)	V _{DRM} , V _{RRM}		V
2N6400		50	
2N6401		100	
2N6402		200	
2N6403		400	
2N6404		600	
2N6405		800	
On-State Current RMS (180° Conduction Angles; T _C = 100°C)	I _{T(RMS)}	16	A
Average On-State Current (180° Conduction Angles; T _C = 100°C)	I _{T(AV)}	10	A
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T _J = 90°C)	I _{TSM}	160	A
Circuit Fusing Considerations (t = 8.3 ms)	I ² t	145	A ² s
Forward Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 100°C)	P _{GM}	20	W
Forward Average Gate Power (t = 8.3 ms, T _C = 100°C)	P _{G(AV)}	0.5	W
Forward Peak Gate Current (Pulse Width ≤ 1.0 μs, T _C = 100°C)	I _{GM}	2.0	A
Operating Junction Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	1.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8 in from Case for 10 Seconds	T _L	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit

OFF CHARACTERISTICS

*Peak Repetitive Forward or Reverse Blocking Current (V _{AK} = Rated V _{DRM} or V _{RRM} , Gate Open)	I _{DRM} , I _{RRM}	-	-	10	μA
T _J = 25°C T _J = 125°C	-	-	-	2.0	mA

ON CHARACTERISTICS

*Peak Forward On-State Voltage (I _{TM} = 32 A Peak, Pulse Width ≤ 1 ms, Duty Cycle ≤ 2%)	V _{TM}	-	-	1.7	V
*Gate Trigger Current (Continuous dc) (V _D = 12 Vdc, R _L = 100 Ω)	I _{GT}	-	9.0	30	mA
T _C = 25°C T _C = -40°C	-	-	-	60	
*Gate Trigger Voltage (Continuous dc) (V _D = 12 Vdc, R _L = 100 Ω)	V _{GT}	-	0.7	1.5	V
T _C = 25°C T _C = -40°C	-	-	-	2.5	
Gate Non-Trigger Voltage (V _D = 12 Vdc, R _L = 100 Ω), T _C = +125°C	V _{GD}	0.2	-	-	V
*Holding Current (V _D = 12 Vdc, Initiating Current = 200 mA, Gate Open)	I _H	-	18	40	mA
T _C = 25°C *T _C = -40°C	-	-	-	60	
Turn-On Time (I _{TM} = 16 A, I _{GT} = 40 mA dc, V _D = Rated V _{DRM})	t _{gt}	-	1.0	-	μs
Turn-Off Time (I _{TM} = 16 A, I _R = 16 A, V _D = Rated V _{DRM}) T _C = 25°C T _J = +125°C	t _q	-	15	-	μs
		-	35	-	

DYNAMIC CHARACTERISTICS

Critical Rate-of-Rise of Off-State Voltage (V _D = Rated V _{DRM} , Exponential Waveform) T _J = +125°C	dv/dt	-	50	-	V/μs
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*Indicates JEDEC Registered Data.

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Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I_H	Holding Current

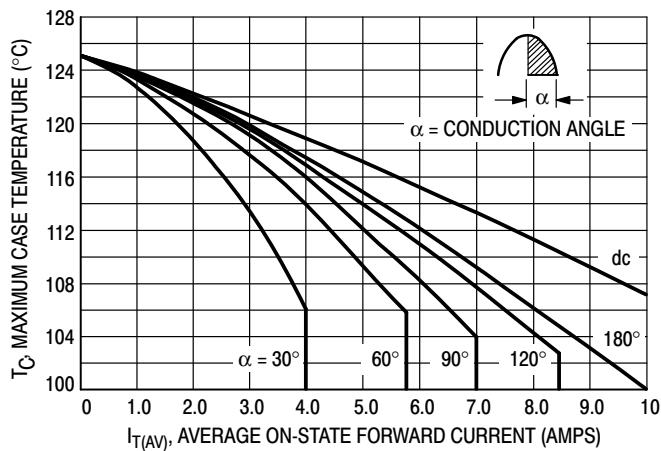
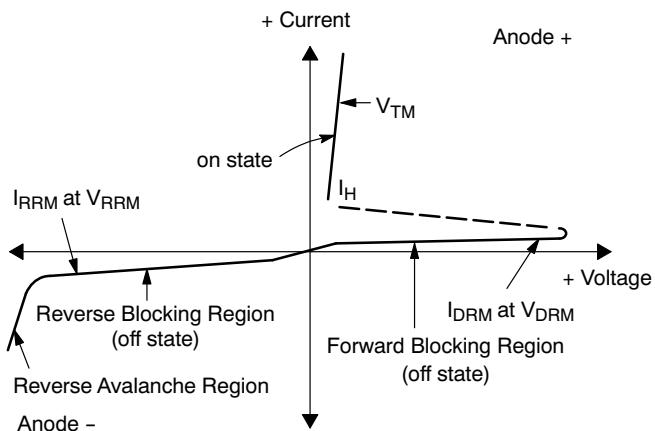


Figure 1. Average Current Derating

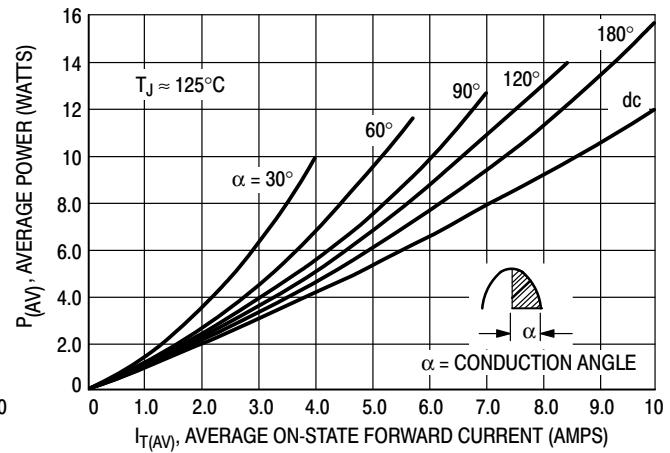


Figure 2. Maximum On-State Power Dissipation

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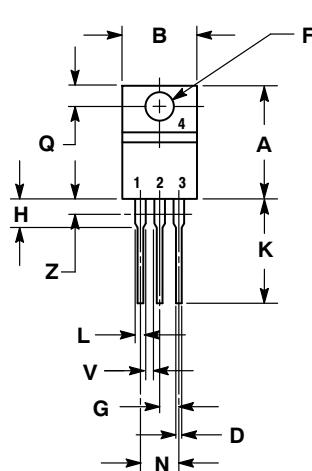
ORDERING INFORMATION

Device	Package	Shipping [†]
2N6400	TO-220AB	500 Units / Box
2N6400G	TO-220AB (Pb-Free)	
2N6401	TO-220AB	
2N6401G	TO-220AB (Pb-Free)	
2N6402	TO-220AB	
2N6402G	TO-220AB (Pb-Free)	
2N6403	TO-220AB	
2N6403G	TO-220AB (Pb-Free)	50 Units / Rail
2N6403TG	TO-220AB (Pb-Free)	
2N6404	TO-220AB	
2N6404G	TO-220AB (Pb-Free)	
2N6405	TO-220AB	500 Units / Box
2N6405G	TO-220AB (Pb-Free)	

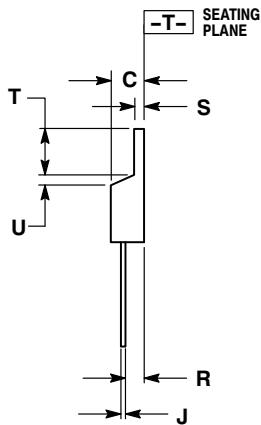
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS



TO-220AB
CASE 221A-07
ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 3:

1. CATHODE
2. ANODE
3. GATE
4. ANODE